

**isc Silicon NPN Power Transistor**
**2SC4134**
**DESCRIPTION**

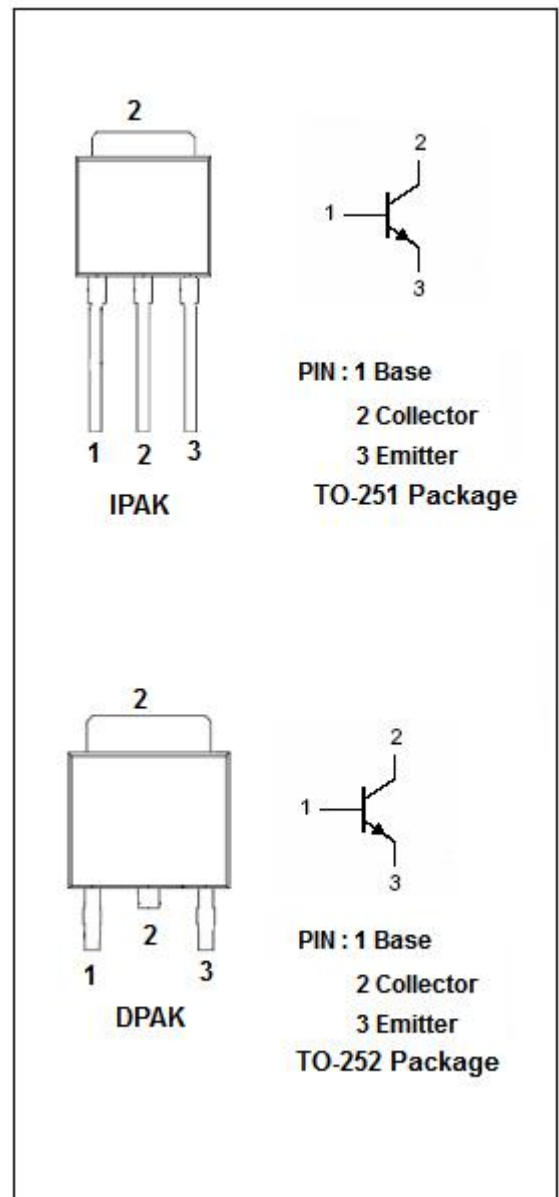
- High voltage and large current capacity
- Fast-speed switching
- Small and slim package permitting 2SC4134-applied sets to be made more compact
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Power supplies, relay drivers, lamp drivers

**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	120	V
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current-Continuous	1	A
I <sub>CM</sub>	Collector Current-Peak	2	A
P <sub>C</sub>	Collector Power Dissipation @ T <sub>C</sub> =25°C	10	W
	Collector Power Dissipation @ T <sub>a</sub> =25°C	0.8	
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C



## isc Silicon NPN Power Transistor

2SC4134

## ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>c</sub> = 0.4A; I <sub>B</sub> = 40mA			0.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>c</sub> = 0.4A; I <sub>B</sub> = 40mA			1.2	V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>c</sub> = 1mA; I <sub>B</sub> = 0	100			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10uA; I <sub>C</sub> = 0	6			V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0			0.1	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			0.1	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>c</sub> = 0.1A; V <sub>CE</sub> = 5V	100		400	
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1.0MHz		8.5		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>c</sub> = 100mA; V <sub>CE</sub> = 10V		120		MHz

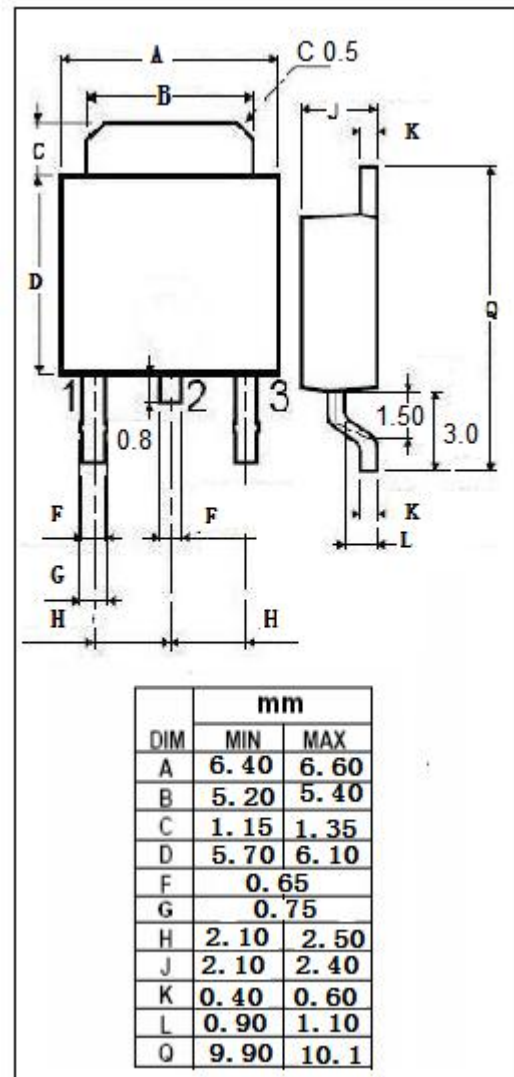
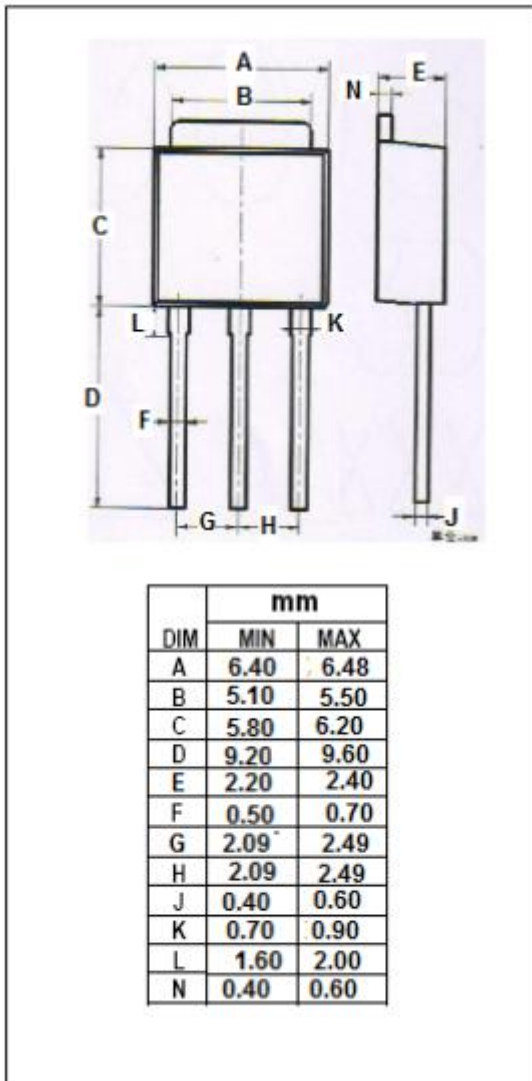
◆ h<sub>FE</sub> Classifications

R	S	T
100-200	140-280	200-400

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Outline Drawing



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